	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	9	sato near atsuhiro.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/11 18:19
2	BRS	L2	145	yamashita near hiroki.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/11 18:20
3	BRS	L3	475	ozawa near yoshio.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/11 18:49

	Type	L #	Hits	Search Text	DBs	Time Stamp
4	BRS	L4	307	438/294.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/11 18:52
5	BRS	L6	4	(inter-electrode near dielectric) near15 (isolat$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/11 18:54
6	BRS	L7	4	(inter near electrode near dielectric) near15 (isolat$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/11 18:54

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L5	155	(inter-electrode near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/11 19:00
8	BRS	L8	4283	(silicon near oxide or sio) near15 (dielectric near constant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/11 19:01
9	BRS	L10	2	((silicon near oxide or sio) near15 (dielectric near constant)) near15 (inter-electrode$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/11 19:02

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L11	2	((silicon near oxide or sio) near15 (dielectric near constant)) near15 (inter near electrode$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/11 19:02
11	BRS	L9	247	((silicon near oxide or sio) near15 (dielectric near constant)) near15 (electrode$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/11 19:15
12	BRS	L12	59	((silicon near oxide or sio) near15 (dielectric near constant)) near15 (ono)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/11 19:06

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	38	((silicon near oxide or sio) near15 (dielectric near constant)) near15 (memory near cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/11 19:06
14	BRS	L14	94	((silicon near oxide or sio) near15 (dielectric near constant)) near15 (conducti$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/11 19:27
15	BRS	L15	2	((silicon near oxide or sio) near15 (dielectric near constant)) near15 (row or column)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/11 19:28

	U	1	Document ID	Title	Current OR
1	X		US 20050003619 A1	Nonvolatile semiconductor memory and manufacturing method for the same	438/294
2	X		US 20050002231 A1	Nonvolatile semiconductor memory and manufacturing method for the same	365/185.01
3	X		US 20020094622 A1	Process flow for a performance enhanced MOSFET with self-aligned, recessed channel	438/197
4	X		US 5792689 A	Double crown capacitor formation for use in DRAM - gives self alignment to node contacts and uses single photoresist masking step	